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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Complete if Known

Application Number	09/945554
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	2826
Examiner Name	Dickey, Thomas

Attorney Docket No: 1303.028US1

Sheet 1 of 2

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
TB	US-5,952,692	09/14/1999	Nakazato, K. , et al.	257	321	10/28/1997
TD	US-6,210,999	04/03/2001	Gardner, , et al.	438	183	12/04/1998
TD	US-6,475,857	11/05/2002	Kim, W. , et al.	438	240	06/21/2001
TD	US-6,541,280	04/01/2003	Kaushik, , et al.			03/20/2001

FOREIGN PATENT DOCUMENTS

Examiner Initials *	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ³
TB		AARIK, JAAN , et al., "Anomalous effect of temperature on atomic layer deposition of titanium oxide", <u>Journal of Crystal Growth</u> , (2000), pp. 531-537	
TD		AARIK, JAAN , et al., "Texture development in nanocrystalline hafnium dioxide thin films grown by atomic layer deposition", <u>Journal of Crystal Growth</u> , (2000), pp. 105-113	
TD		FERGUSON, J D., et al., "Atomic layer deposition of Al ₂ O ₃ and SiO ₂ on BN particles using sequential surface reaction", <u>Applied Surface Science</u> , (2000), pp. 280-292	
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TD		KIM, YEONG K., et al., "Novel capacitor technology for high density stand-alone and embedded DRAMs", <u>IEEE</u> , (2000), 4 pages	
TD		KUKLI, KAUPU , "Atomic Layer Deposition of Titanium Oxide from TiI ₄ and H ₂ O ₂ ", <u>Chemical Vapor Deposition</u> , (2000), pp. 303-310	
TD		KUKLI, KAUPU , et al., "Atomic layer deposition of zirconium oxide from zirconium tetraiodide, water and hydrogen peroxide", <u>Journal of Crystal Growth</u> , (2001), pp. 262-272	
TD		KUKLI, KAUPU , et al., "Real-time monitoring in atomic layer deposition of TiO ₂ from TiI ₄ and H ₂ O-H ₂ O ₂ ", <u>American Chemical Society</u> , (2000), pp. 8122-8128	
TD		LEE, J. , "Effect of Polysilicon Gate on the Flatband Voltage Shift and Mobility Degradation for ALD-Al ₂ O ₃ Gate Dielectric", <u>IEDM</u> , (2000), pp. 645-648	
TD		PARANJPE, AJIT , et al., "Atomic layer deposition of AlO _x for thin film head gap application", <u>Journal of the Electrochemical Society</u> , (September 2001), pp. 465-471	

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TO	SMITH, RYAN C., et al., "Chemical vapour deposition of the oxides of titanium, zirconium and hafnium for use as high-k materials in microelectronic devices. A carbon-free precursor for the synthesis of hafnium dioxide", <u>Advanced Materials for Optics and Electronics</u> , (2000), 2 pages
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* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 908. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. Applicant's unique citation designation number (optional) Applicant is to place a check mark here if English language Translation is attached